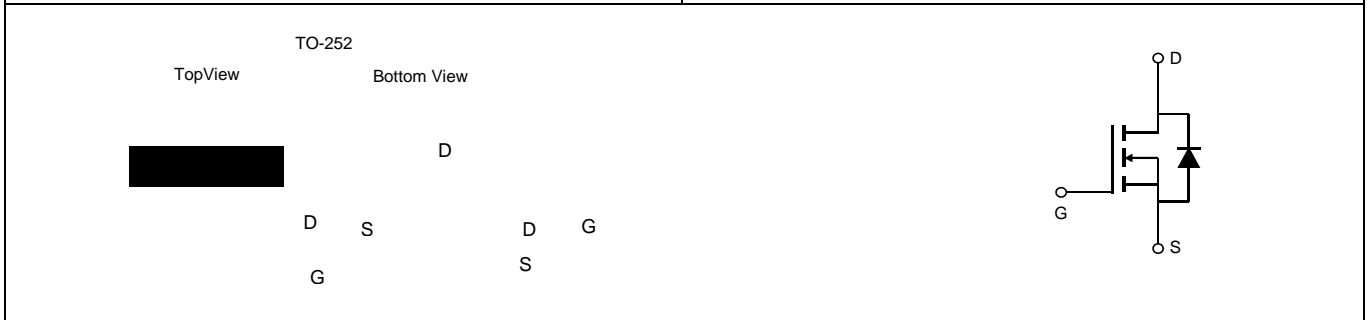


TMD80N04D

N-CHANNEL ENHANCEMENT MOSFET

<p>General Description</p> <p>7K70' 1 ' XVHV DGYDQFHG WUHQFK GHVLJQ WR SURYLGH ZHWHFH QZQJWVH ,W FDQ EH XVHG LQ D ZLGH YDULHW</p>	<p>Product Summary</p> <p>VDS=40V, ID=80A DQG RDS(ON) <7m @ VGS=10V</p>
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Absolute Maximum Ratings (T_c=25°C unless otherwise noted)			
Parameter	Symbol	Limit	Unit
Drain-Source Voltage	V _{DS}	40	V
Gate-Source Voltage	V _{GS}	±20	V
Drain Current-Continuous	I _D	80	A
Drain Current-Continuous(T _c =100°C)	I _D (100°C)	56	A
Pulsed Drain Current	I _{DM}	350	A
Maximum Power Dissipation	P _D	80	W
Derating factor		0.53	W/°C
Single pulse avalanche energy ^(Note 5)	E _{AS}	750	mJ
Operating Junction and Storage Temperature Range	T _J ,T _{STG}	-55 To 175	°C
Thermal Resistance,Junction-to-Case ^(Note 2)	R _{θJC}	1.88	°C/W

Electrical Characteristics (T_C=25°C unless otherwise noted)

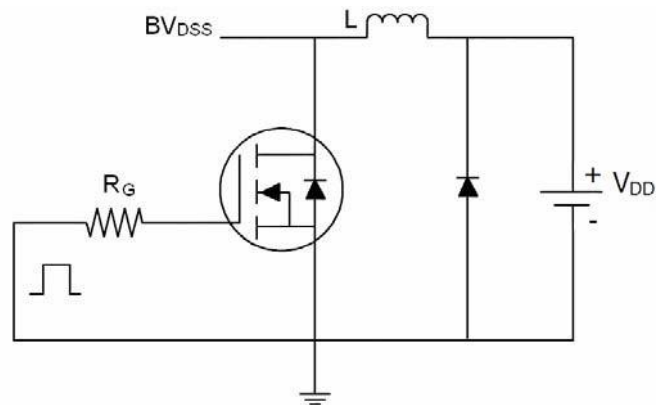
Parameter	Symbol	Condition	Min	Typ	Max	Unit
Off Characteristics						
Drain-Source Breakdown Voltage	BV _{DSS}	V _{GS} =0V, I _D =250μA	40	45	-	V
Zero Gate Voltage Drain Current	I _{DSS}	V _{DS} =40V, V _{GS} =0V	-	-	1	μA
Gate-Body Leakage Current	I _{GSS}	V _{GS} =±20V, V _{DS} =0V	-	-	±100	nA
On Characteristics (Note 3)						
Gate Threshold Voltage	V _{GS(th)}	V _{DS} =V _{GS} , I _D =250μA	1.2	1.8	2.5	V
Drain-Source On-State Resistance	R _{DS(on)}	V _{GS} =10V, I _D =20A	-	-	7	m
Forward Transconductance	g _{FS}	V _{DS} =10V, I _D =20A	15	-	-	S
Dynamic Characteristics (Note4)						
Input Capacitance	C _{iss}	V _{DS} =20V, V _{GS} =0V, F=1.0MHz	-	-	2320	PF
Output Capacitance	C _{oss}		-	-	189	PF
Reverse Transfer Capacitance	C _{rss}		-	-	140	PF
Switching Characteristics (Note 4)						
Turn-on Delay Time	t _{d(on)}	V _{DD} =20V, R _L =1 V _{GS} =10V, R _G =3	-	12	-	nS
Turn-on Rise Time	t _r		-	11	-	nS
Turn-Off Delay Time	t _{d(off)}		-	39	-	nS
Turn-Off Fall Time	t _f		-	12	-	nS
Total Gate Charge	Q _g	V _{DS} =20V, I _D =20A, V _{GS} =10V	-	61	-	nC
Gate-Source Charge	Q _{gs}		-	15.3	-	nC
Gate-Drain Charge	Q _{gd}		-	14.5	-	nC
Drain-Source Diode Characteristics						
Diode Forward Voltage (Note 3)	V _{SD}	V _{GS} =0V, I _S =10A	-	-	1.2	V
Diode Forward Current (Note 2)	I _S		-	-	80	A
Reverse Recovery Time	t _{rr}	T _J = 25°C, I _F = 20A di/dt = 100A/μs (Note3)	-	-	45	nS
Reverse Recovery Charge	Q _{rr}		-	-	50	nC

Notes:

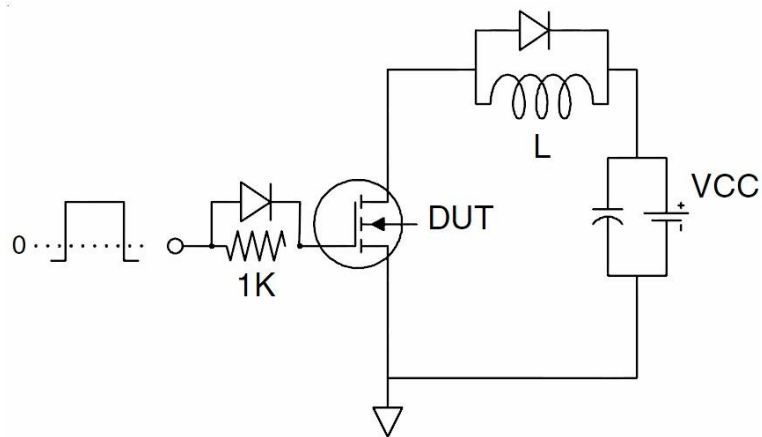
1. Repetitive Rating: Pulse width limited by maximum junction temperature.
2. Surface Mounted on FR4 Board, t ≤ 10 sec.
3. Pulse Test: Pulse Width ≤ 300μs, Duty Cycle ≤ 2%.
4. Guaranteed by design, not subject to production
5. E_{AS} condition : T_J=25°C, V_{DD}=20V, V_G=10V, L=1mH, R_G=25 , I_{AS}=42A

Test circuit

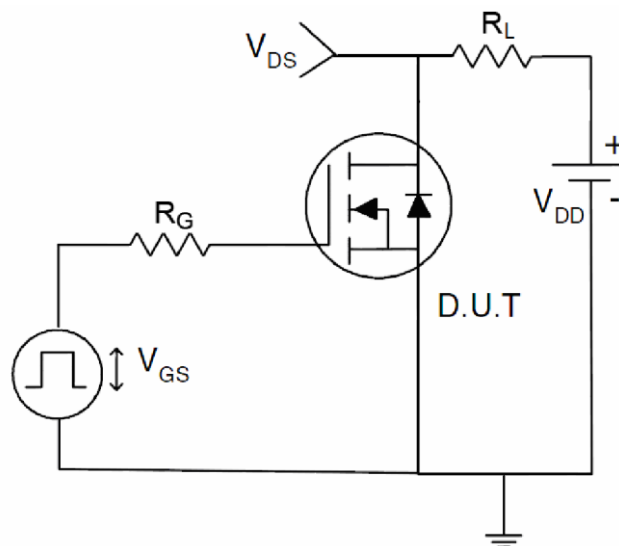
1) EAS Test Circuit



2) Gate Charge Test Circuit



3) Switch Time Test Circuit



Typical Electrical and Thermal Characteristics (Curves)

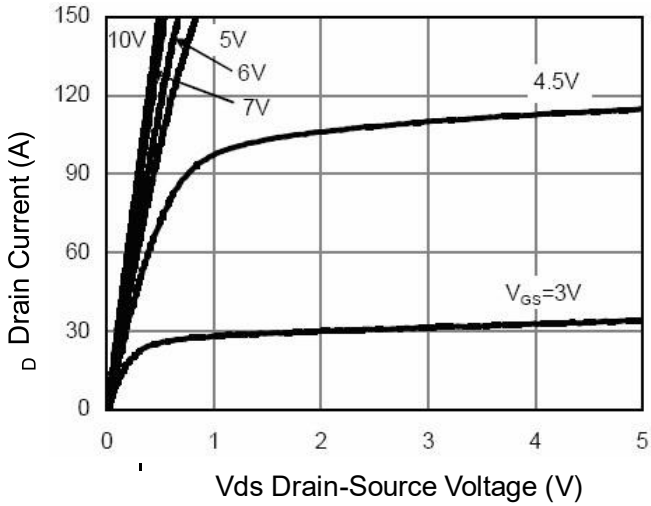


Figure 1 Output Characteristics

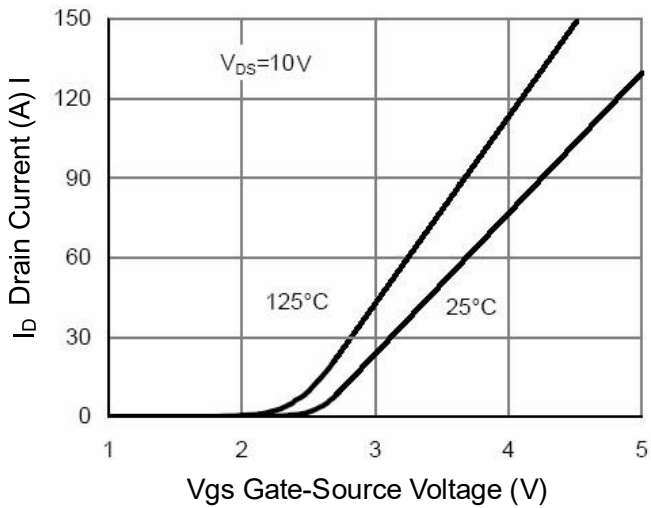


Figure 2 Transfer Characteristics

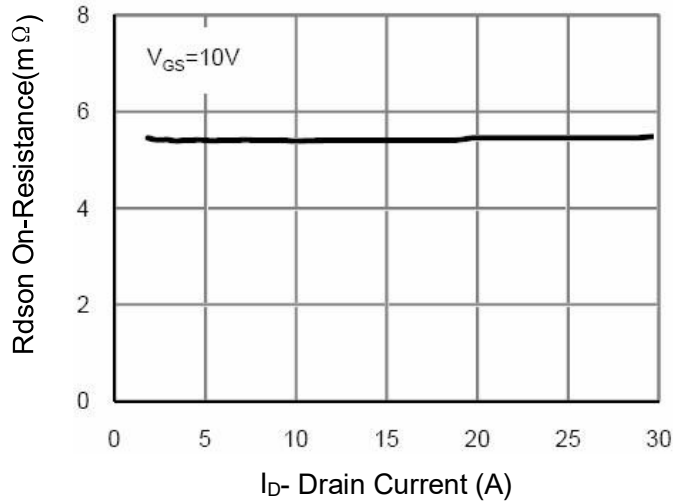


Figure 3 Rdson-Drain Current

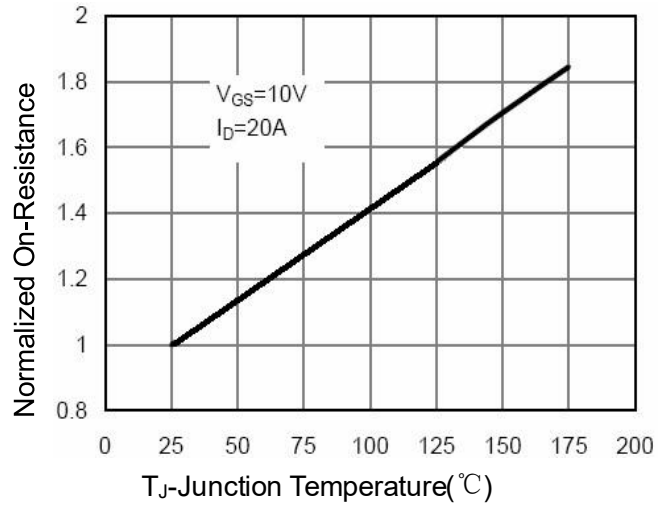


Figure 4 Rdson-Junction Temperature

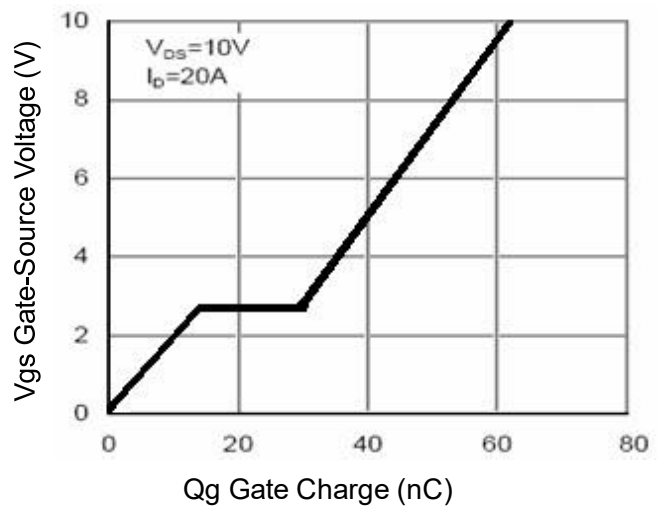


Figure 5 Gate Charge

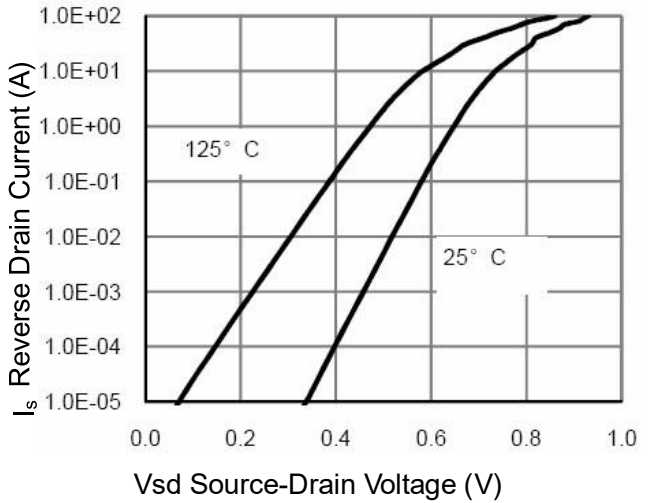


Figure 6 Source-Drain Diode Forward

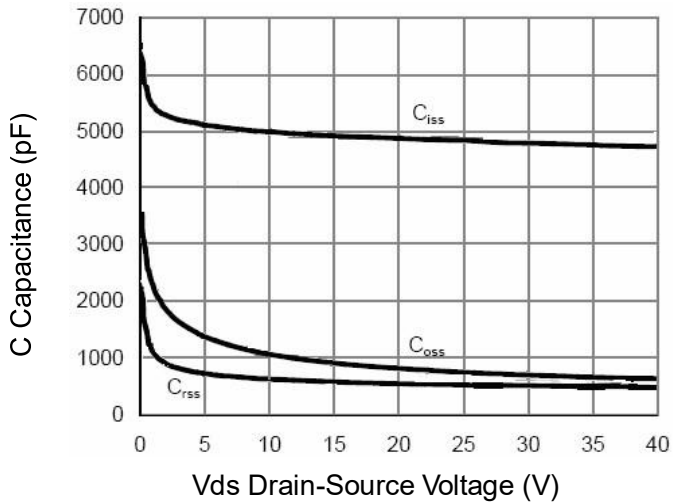


Figure 7 Capacitance vs Vds

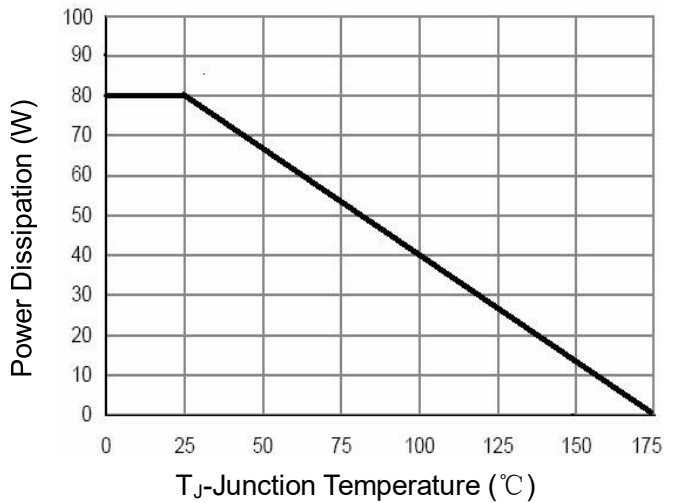


Figure 9 Power De-rating

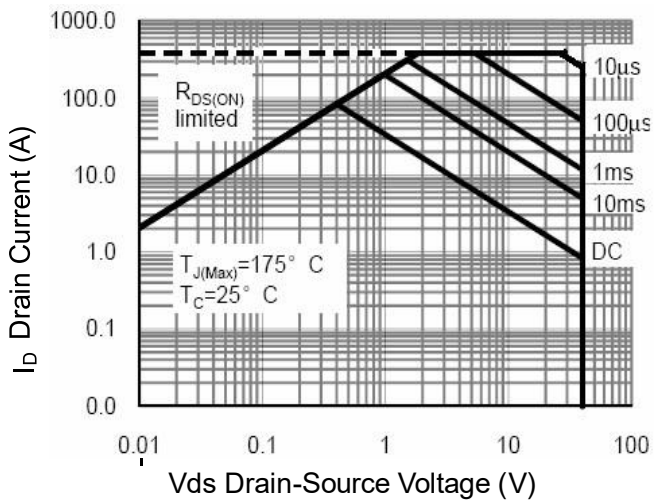


Figure 8 Safe Operation Area

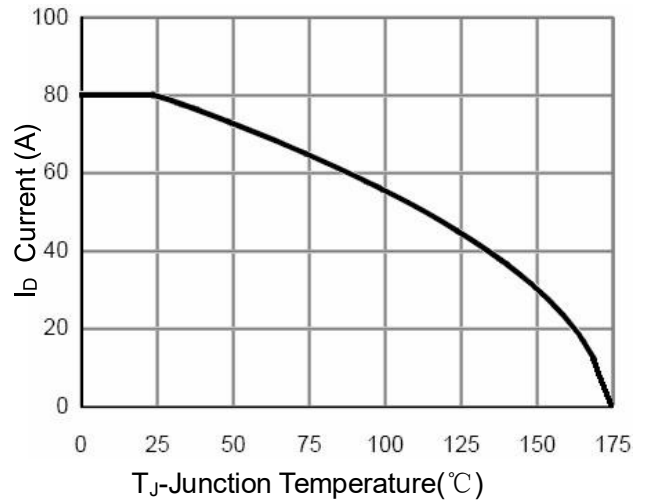
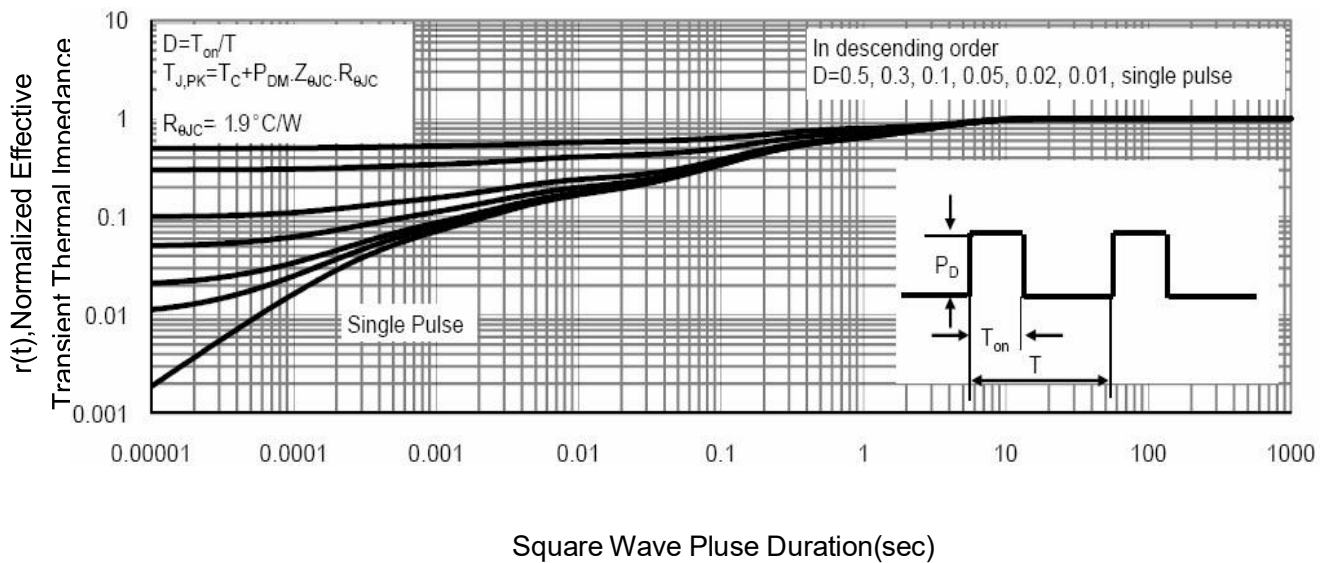
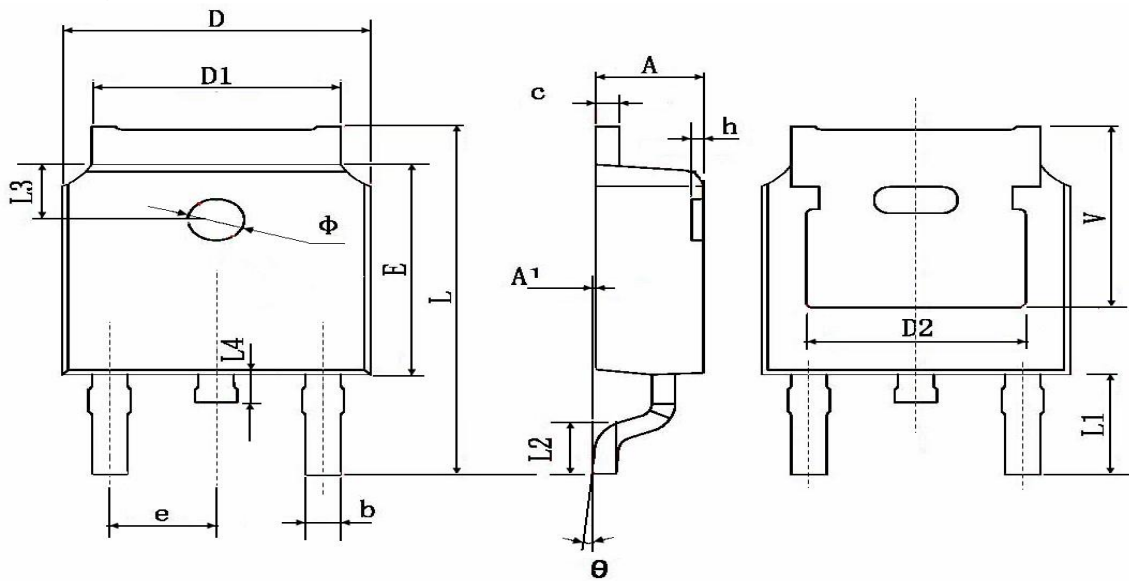


Figure 10 ID Current- Junction Temperature



TO-252 Package Information



Symbol	Dimensions In Millimeters		Dimensions In Inches	
	Min.	Max.	Min.	Max.
A	2.200	2.400	0.087	0.094
A1	0.000	0.127	0.000	0.005
b	0.660	0.860	0.026	0.034
c	0.460	0.580	0.018	0.023
D	6.500	6.700	0.256	0.264
D1	5.100	5.460	0.201	0.215
D2	4.830 TYP.		0.190 TYP.	
E	6.000	6.200	0.236	0.244
e	2.186	2.386	0.086	0.094
L	9.800	10.400	0.386	0.409
L1	2.900 TYP.		0.114 TYP.	
L2	1.400	1.700	0.055	0.067
L3	1.600 TYP.		0.063 TYP.	
L4	0.600	1.000	0.024	0.039
Φ	1.100	1.300	0.043	0.051
θ	0°	8°	0°	8°
h	0.000	0.300	0.000	0.012
V	5.350 TYP.		0.211 TYP.	